

**D882** TRANSISTOR ( NPN )

**FEATURES**

Power dissipation

$$P_{CM} : 1.25 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

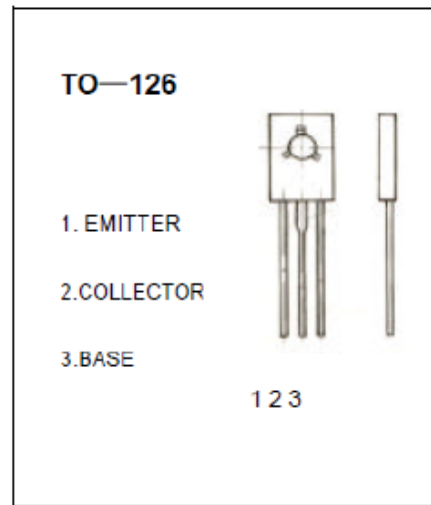
$$I_{CM} : 3 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : 40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



**ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100 \mu\text{A}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100 \mu\text{A}, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=40\text{V}, I_E=0$			1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE}=30\text{V}, I_B=0$			10	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=6\text{V}, I_C=0$			1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=2\text{V}, I_C=1\text{A}$	60		400	
	$h_{FE(2)}$	$V_{CE}=2\text{V}, I_C=100\text{mA}$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{A}, I_E=0.2\text{A}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2\text{A}, I_E=0.2\text{A}$			1.5	V
Transition frequency	$f_T$	$V_{CE}=5\text{V}, I_C=0.1\text{mA}$ $f=10\text{MHz}$	50			MHz

**CLASSIFICATION OF  $h_{FE(1)}$**

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400